

Snubberless™, logic level and standard 12 A Triacs

Datasheet - production data

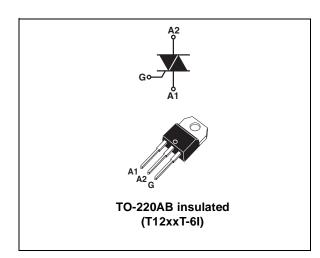


Table 1. Device summary

Part number	Symbol	Value
T1210T-6I	I _{GT} 3Q logic level	10 mA
T1220T-6I T1235T-6I	I _{GT} 3Q Snubberless	20 / 35 mA
T1225T-6I	I _{GT} 4Q standard	25 mA

Features

- Medium current Triac
- High static and dynamic commutation
- · Low thermal resistance with clip bonding
- Packages is RoHS (2002/95/EC) compliant
- 600 V V_{RM}
- UL certified (ref. file E81734)

Applications

- · Value sensitive application
- · General purpose ac line load switching
- Motor control circuits in power tools
- · Small home appliances, lighting
- · Inrush current limiting circuits
- Overvoltage crowbar protection

Description

Available in through-hole, the T12T series of Triacs can be used as on/off or phase angle control function in general purpose AC switching where high commutation capability is required.

This series can be designed in many value sensitive appliances thanks to the parameters guidance provided in the following pages.

Provides insulation rated at 2500 V rms (TO-220AB insulated package).

TM: Snubberless is a trademark of STMicroelectronics

Characteristics T12T

1 Characteristics

Table 2. Absolute maximum ratings (limiting values; $T_j = 25$ °C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
I _{T(RMS)}	On-state rms current (full sine wave) $T_c = 88 ^{\circ}\text{C}$			12	Α
1.	Non repetitive surge peak on-state current (full	F = 50 Hz	t _p = 20 ms	90	Α
I _{TSM}	cycle, T _j initial = 25 °C)	F = 60 Hz	$t_p = 16.7 \text{ ms}$	95	A
l ² t	I^2t Value for fusing $t_p = 10 \text{ ms}$			54	A ² s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ $F = 60 \text{ Hz}$ $T_j = t_r \le 100 \text{ ns}$		T _j = 125 °C	50	A/µs
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state voltage $t_p = 10 \text{ ms}$ $T_j = 10 \text{ ms}$		T _j = 25 °C	V _{DRM} , V _{RRM} + 100	V
I _{GM}	Peak gate current $t_p = 20 \mu s$ $T_j = 125 ^{\circ} C$		4	Α	
P _{G(AV)}	Average gate power dissipation $T_j = 125 \text{ °C}$				W
T _{stg}	Storage junction temperature range			- 40 to + 150	°C
Tj	Operating junction temperature range				°C



T12T Characteristics

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Complete	Toot conditions	Quadrant		T12xxT			l loo!t	
Symbol	Test conditions	Quadrant		T1210T	T1220T	T1225T	T1235T	Unit
I _{GT} ⁽¹⁾	$V_D = 12 \text{ V} R_L = 30 \Omega$	1 - 11 - 111	MAX.	10	20	25	35	mA
'GT`		IV				40		
V _{GT}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega,$ $T_j = 25 \text{ °C}$ ALL		MAX.	1.3			V	
V _{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$, $T_j = 125 \text{ °C}$	ALL	MIN.	0.2		V		
I _H ⁽²⁾	I _T = 500 mA		MAX.	10	15	20	30	mA
	I _G = 1.2 I _{GT}	I - III		20	35	40	50	
IL		IV	MAX.			40		mA
		II		30	40	60	80	
dV/dt (2)	V _D = 67% V _{DRM} , gate open	T _j = 125 °C	MIN.	100	1000	100	2000	V/µs
u v/ui · /		$T_j = 150 {}^{\circ}C^{(3)}$		50	500	50	1000	
	(dV/dt)c = 0.1 V/μs			7		7		
	(dV/dt)c = 10 V/µs	T _j = 125 °C		3		3		
(dl/dt)c (2)	Without snubber				6		12	A /m c
	(dV/dt)c = 0.1 V/μs		MIN.	3		3		A/ms
	(dV/dt)c = 10 V/µs	$T_j = 150 {}^{\circ}C^{(3)}$		1		1		
	Without snubber				3		10	

- 1. Minimum $I_{\mbox{\footnotesize{GT}}}$ is guaranteed at 5% of $I_{\mbox{\footnotesize{GT}}}$ max.
- 2. For both polarities of A2 referenced to A1.
- 3. Derating information for excess temperature above $T_j \, \text{max}$.

Table 4. Static characteristics

Symbol	Test conditions				Unit
V _T ⁽¹⁾	I _{TM} = 17 A, t _p = 380 μs	T _j = 25 °C	MAX.	1.55	V
V _{TO} (1)	Threshold voltage	T _j = 125 °C	MAX.	0.85	V
R _D ⁽¹⁾	Dynamic resistance	T _j = 125 °C	MAX.	35	mΩ
I _{DRM}	$V_{DRM} = V_{RRM}$	T _j = 25 °C	MAX.	5	μA
		T _j = 125 °C		1	0
	$V_D = 0.9 \times V_{DRM}$	$T_j = 150 ^{\circ}C^{(2)}$	TYP.	1.9	mA

- 1. For both polarities of A2 referenced to A1.
- 2. Derating information for excess temperature above $\mathsf{T}_{j}\,\mathsf{max}.$

Characteristics T12T

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	2.6	°C/W
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus rms on-state current (full cycle)

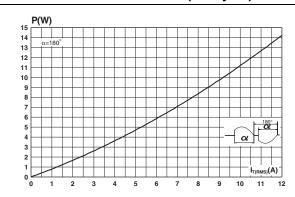


Figure 2. On-state rms current versus case temperature (full cycle)

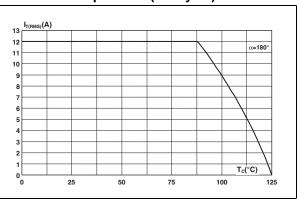
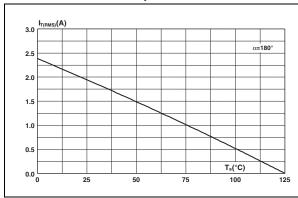


Figure 3. On-state rms current versus ambient temperature

Figure 4. Relative variation of thermal impedance versus pulse duration



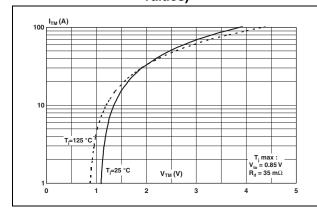
1.0E+00 K=[Z₀/R_m]

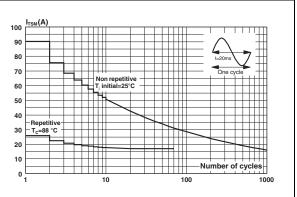
1.0E-01 Z_{0(c2)}

1.0E-02 1.0E-01 1.0E+00 1.0E+01 1.0E+03

Figure 5. On state characteristics (maximum values)

Figure 6. Surge peak on state current versus number of cycles



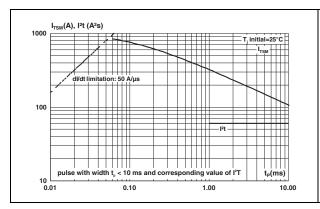


4/8 DocID16487 Rev3

T12T Characteristics

Figure 7. Non repetitive surge peak on state current for a sinusoidal

Figure 8. Relative variation of gate trigger current and gate trigger voltage versus junction temperature



2.5 typical values

2.6 typical values

2.7 typical values

1.8 typical values

1.9 typical values

1.0 typical values

1.1 typical values

1.2 typical values

1.3 typical values

1.4 typical values

1.5 typical values

1.6 typical values

1.7 typical values

1.7 typical values

1.8 typical values

1.9 typical values

1.0 typical values

1.1 typical values

1.1 typical values

1.1 typical values

1.2 typical values

1.3 typical values

1.5 typical values

1.5 typical values

1.6 typical values

1.7 typical values

1.7 typical values

1.8 typical values

1.8 typical values

1.9 typical values

1.0 typical values

1.0 typical values

1.0 typical values

1.0 typical values

1.1 typical values

1.5 typical values

1.0 typical values

1.1 typical values

1.1 typical values

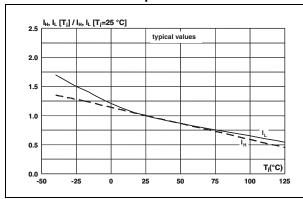
1.1 typical values

1.2 typical values

1.5 ty

Figure 9. Relative variation of holding current and latching current versus junction temperature

Figure 10. Relative variation of critical rate of decrease of main current versus (dV/dt)c



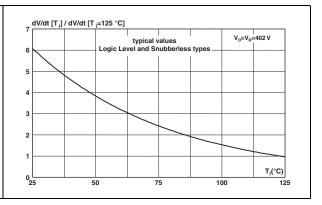
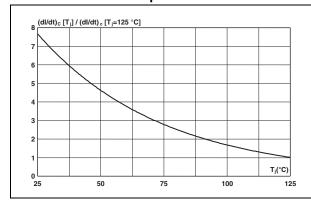
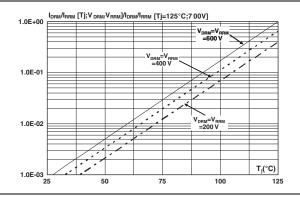


Figure 11. Relative variation of critical rate of decrease of main current versus junction temperature

Figure 12. Leakage current versus junction temperature for different values of blocking voltage (typical values)





Package information **T12T**

2 **Package information**

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Dimensions Ref. **Millimeters** Inches Min. Тур. Max. Min. Тур. Max. Α 15.20 15.90 0.598 0.625 a1 3.75 0.147 a2 13.00 14.00 0.511 0.551 Ø١ 10.40 0.393 0.409 В 10.00 ÎL 0.024 0.034 b1 0.61 0.88 0.048 0.051 b2 1.23 1.32 14 С 4.40 4.60 0.173 0.181 0.027 0.49 0.70 0.019 с1 c2 2.72 0.094 0.107 c2 2.40 a2 0.094 0.106 е 2.40 2.70 F 6.20 6.60 0.244 0.259 0.151 Ø١ 3.75 3.85 0.147 14 15.80 16.40 16.80 0.622 0.646 0.661 0.116 L 2.65 2.95 0.104 12 1.14 1.70 0.044 0.066 13 1.14 1.70 0.044 0.066 Μ 2.60 0.102

Table 6. TO-220AB insulated dimensions



DocID16487 Rev3 6/8

T12T Ordering information

3 Ordering information

Figure 13. Ordering information scheme

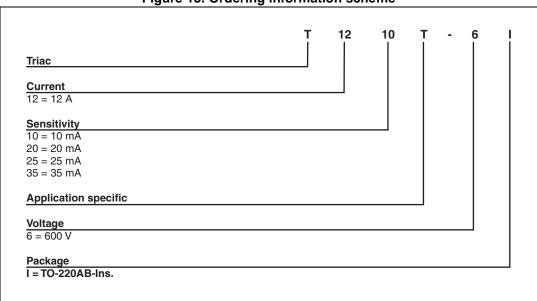


Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1210T-6I	T1210T-6I				
T1220T-6I	T1220T-6I	TO-220AB-ins.	2.3 g	50	Tube
T1225T-6I	T1225T-6I	10-220AD-1118.	2.5 g	30	rube
T1235T-6I	T1235T-6I				

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
03-Dec-2009	1	Initial release.
18-Jan-2010	2	Updated pag.1.
16-Sep-2013	3	Updated: Features. Replaced order codes with part numbers in Table 1.



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

ST PRODUCTS ARE NOT DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2013 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

8/8 DocID16487 Rev3